

Name:  
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Section Number: 01/02/03 A/B  
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Dr Ahmad Wafi  
Table Number:



**College of Engineering**  
Department of Electrical and Electronics Engineering

**Test 2**

**SEMESTER 1, ACADEMIC YEAR 2019/2020**

Subject Code : **EEEEB2014/EEEEB273**  
Course Title : **Electronics Analysis & Design II**  
Date : **17 August 2019**  
Time Allowed : **2 hours**

**Instructions to the candidates:**

1. Write your Name and Student ID Number. Indicate your Section Number and Lecturer's Name. Write also your Table Number.
2. **Write all your answers using pen. DO NOT USE PENCIL** except for the diagram.
3. **ANSWER ALL QUESTIONS.** Show clearly all your calculations. Every value **must** be written with its correct Unit.
4. **WRITE YOUR ANSWER ON THIS QUESTION PAPER.**

**NOTE: DO NOT OPEN THE QUESTION PAPER UNTIL INSTRUCTED TO DO SO.**

☺ **GOOD LUCK!** ☺

| Question Number | Q1 (abc) | Q1 (d) | Q2 (a) | Q2 (b) | Q3 (ab) | Q4 (a) | Q4 (b) | Total |
|-----------------|----------|--------|--------|--------|---------|--------|--------|-------|
| Marks           |          |        |        |        |         |        |        |       |

## BASIC FORMULA FOR TRANSISTOR

### BJT

$$i_C = I_S e^{v_{BE}/V_T}; \text{npn}$$

$$i_C = I_S e^{v_{EB}/V_T}; \text{pnp}$$

$$i_C = \alpha i_E = \beta i_B$$

$$i_E = i_B + i_C$$

$$\alpha = \frac{\beta}{\beta + 1}$$

; Small signal

$$\beta = g_m r_\pi$$

$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 26 \text{ mV}$$

Quadratic formula :

$$Ax^2 + Bx + C = 0 \quad \rightarrow \quad x = \frac{-B \pm \sqrt{B^2 - 4AC}}{2A}$$

### MOSFET

; N – MOSFET

$$v_{DS}(\text{sat}) = v_{GS} - V_{TN}$$

$$i_D = K_n [v_{GS} - V_{TN}]^2$$

$$K_n = \frac{k'_n}{2} \cdot \frac{W}{L}$$

; P – MOSFET

$$v_{SD}(\text{sat}) = v_{SG} + V_{TP}$$

$$i_D = K_p [v_{SG} + V_{TP}]^2$$

$$K_p = \frac{k'_p}{2} \cdot \frac{W}{L}$$

; Small signal

$$g_m = 2\sqrt{K_n I_{DQ}} \quad ; \text{N - MOSFET}$$

$$g_m = 2\sqrt{K_p I_{DQ}} \quad ; \text{P - MOSFET}$$

$$r_o \cong \frac{1}{\lambda I_{DQ}}$$

**QUESTION 1 [30 marks]**

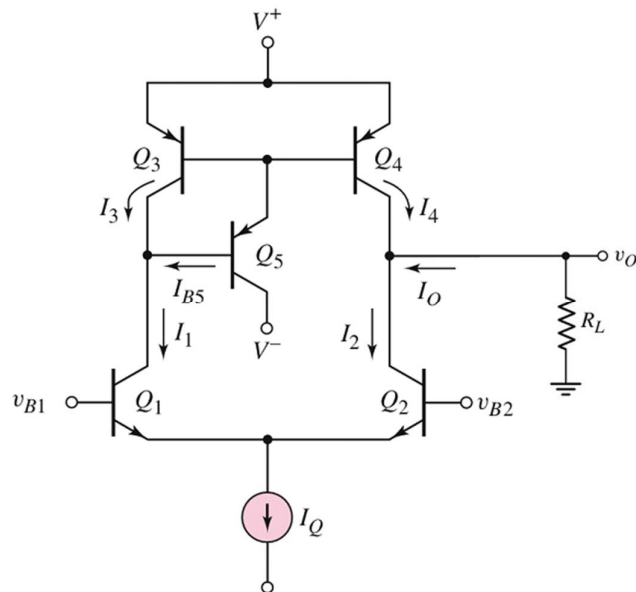
The differential amplifier with active load shown in **Figure 1** has a pair of **npn bipolar differential amplifier** as input devices and a pair of **pnp bipolar connected as an active load**. It is given that  $V^+ = 5\text{ V}$ ,  $V^- = -5\text{ V}$ , and  $I_Q = 0.4\text{ mA}$ . The transistor parameters are shown in Table 1 below.

**Table 1: BJT parameters**

| npn transistor                      | pnp transistor                      |
|-------------------------------------|-------------------------------------|
| $\beta_n = 200$                     | $\beta_p = 150$                     |
| $V_{BE}(\text{on}) = 0.67\text{ V}$ | $V_{EB}(\text{on}) = 0.65\text{ V}$ |
| $V_{An} = 100\text{ V}$             | $V_{Ap} = 70\text{ V}$              |

- (a) Calculate the voltages  $V_{EC4}$  and  $V_{CE2}$  such that the DC voltages are balanced. It is given that  $v_{B1} = v_{B2} = 0$ . [8 marks]
- (b) Find the open-circuit differential-mode voltage gain,  $A_d$ . [6 marks]
- (c) Calculate the value of a load resistance  $R_L$  connected to the output  $v_O$  if the differential mode voltage gain  $A_d$  is to be reduced to 90% of the open-circuit gain. [6 marks]
- (d) Draw pnp bipolar differential amplifier with npn two-transistor active load. The current source  $I_Q$  is implemented with a Widlar current source. Label the diagram clearly, showing all necessary currents, resistors, and BJTs used in the circuit. [10 marks]

**Answers for Question 1**



**Figure 1**

**Answers for Question 1 (Continued)**

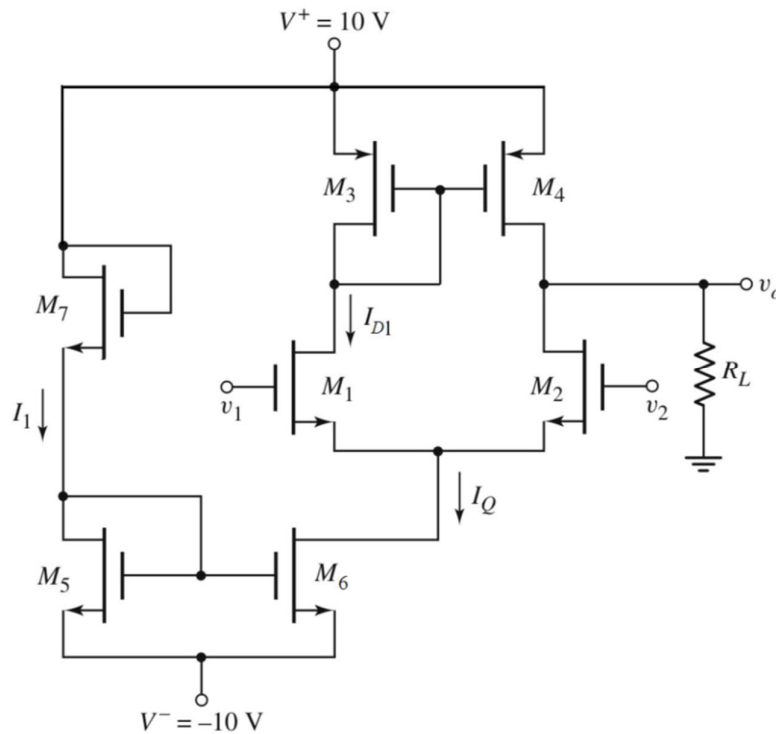
**QUESTION 2** [35 marks]

- (a) Consider an **NMOS differential amplifier with cascode active load**, where the bias current ( $I_Q$ ) is generated using a **Wilson Current Mirror**. Draw the **NMOS cascode active load differential amplifier**. Label  $M_1$  and  $M_2$  for differential pair,  $M_3 - M_6$  for load and  $M_7 - M_9$  for current biasing circuit. Also clearly label the input ( $v_1, v_2$ ) and output  $v_o$ . [8 Marks]

**Answers for Question 2(a)**

(b) Consider the differential amplifier circuit in **Figure 2**. All the NMOS transistors have the same  $K_n = 0.2 \text{ mA/V}^2$ ,  $V_{TN} = 2 \text{ V}$ , and  $\lambda_n = 0.015 \text{ V}^{-1}$ . The active load transistors are matched with parameters  $K_p = 0.1 \text{ mA/V}^2$ ,  $V_{TP} = -2 \text{ V}$ , and  $\lambda_p = 0.02 \text{ V}^{-1}$ . The biasing current,  $I_Q$  is **12.8 mA**.

- (i) Calculate the **output resistance  $R_O$**  of the differential amplifier [5 marks]
- (ii) Calculate the **open circuit differential-mode gain** [5 marks]
- (iii) The output of the amplifier is connected with **10k $\Omega$  load**. Find the differential mode voltage gain. [5 marks]
- (iv) The **Common-Mode Rejection Ratio (CMRR)** was measured to be **27.7 dB**. Using **CMRR equation**, calculate the **common-mode voltage gain,  $A_{CM}$**  of the amplifier? [5 marks]
- (v) Calculate the output voltage,  $v_o$  if the differential input voltage is  $v_1 = 10.5 \sin(\omega t) \text{ V}$  and  $v_2 = -9.5 \sin(\omega t) \text{ V}$ . [7 marks]



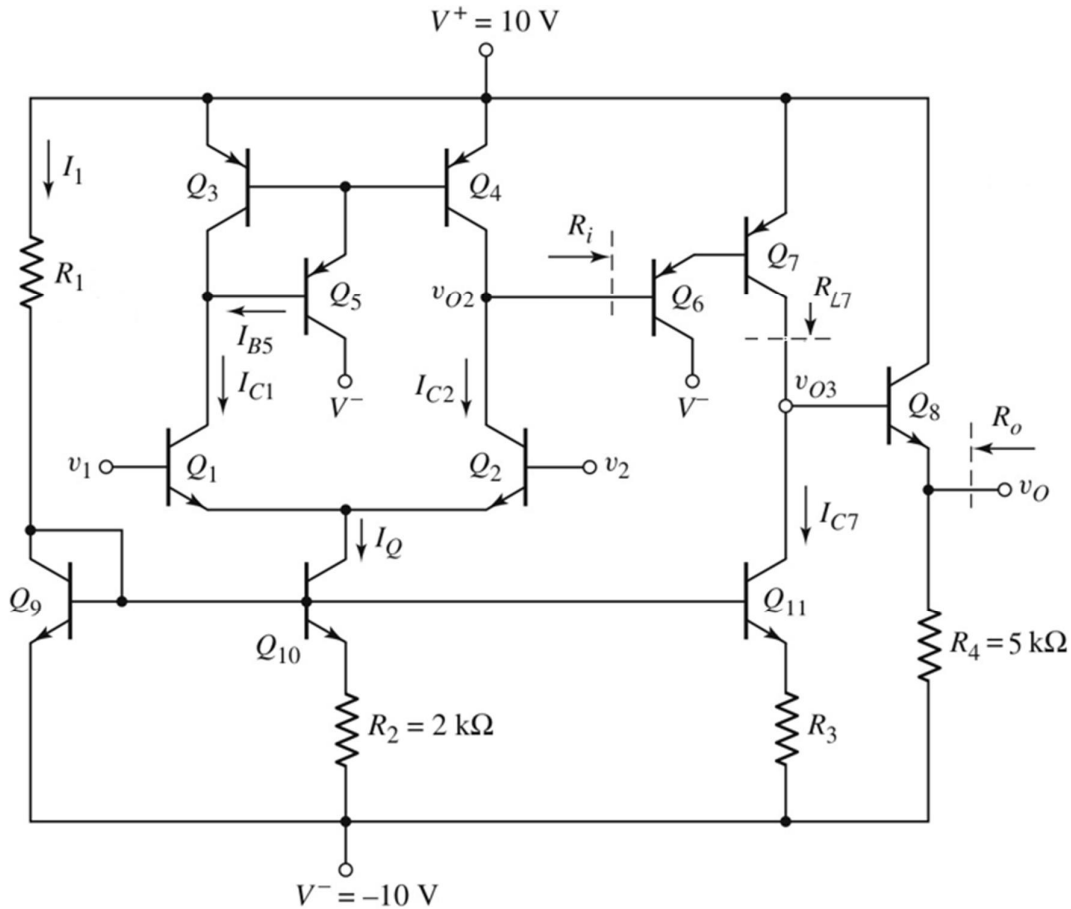
**Figure 2**

**Answers for Question 2(b)**

**QUESTION 3 [20 marks]**

The circuit in **Figure 3** shows a simple multi-stage BJT op-amp, consisting of 3 different stages and bias circuit. It is given that  $V_{BE(on)} = 0.6\text{ V}$ ,  $V_A = 120\text{ V}$ , and  $\beta = 120$  for all transistors.

Assume  $I_{C7} = I_Q = 45\ \mu\text{A}$ . Also, the output voltage,  $v_o = 0\text{ V}$  for  $v_1 = v_2 = 0\text{ V}$ .



**Figure 3**

(a) Calculate the input resistance ( $R_i$ ) and the load resistance ( $R_{L7}$ ) for the Darlington Pair in the gain stage as indicated in the **Figure 3**. [15 marks]

(b) Calculate the voltage gain of the gain stage ( $A_2$ ), where  $A_2 = v_{O3}/v_{O2}$  is derived from the following relationships:

$$v_{O3} = I_{C7} (r_{o7} \parallel R_{L7})$$

$$v_{O2} = I_{B6} R_i$$

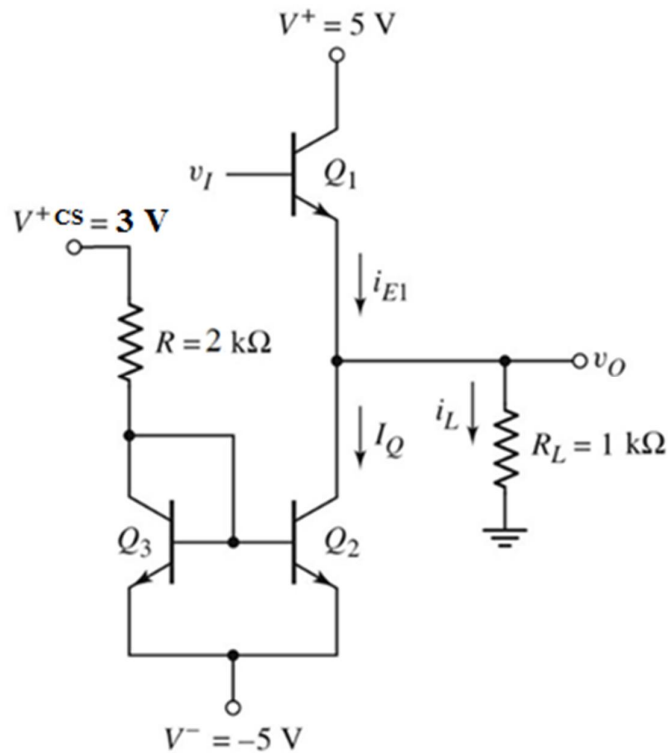
[5 marks]



**Answers for Question 3**

**QUESTION 4 [15 marks]**

- (a) **Compare** the performance of both **Class-A** and **Class-B** output stages in terms of **power conversion efficiency,  $\eta$** . [3 marks]
- (b) Consider the **Class-A emitter-follower** circuit shown in **Figure 4**. Study the **Figure 4 thoroughly**. Assume all transistors are matched with  $V_{BE(\text{on})} = 0.6 \text{ V}$ ,  $V_{CE(\text{sat})} = 0.2 \text{ V}$ , and  $V_A = \infty$ . **Neglect** base currents.

**Figure 4**

- (i) **Find** the value of  $I_Q$ . [2 marks]
- (ii) For  $v_O = 0 \text{ V}$ , **calculate** the power dissipated individually in transistor  $Q_1$ ,  $Q_2$ , and  $Q_3$ , and also the power dissipated in resistor  $R$ . [6 marks]
- (iii) **Determine** the power conversion efficiency ( $\eta$ ) for a symmetrical sine-wave output voltage ( $v_O$ ) with peak value of **4 V**. [4 marks]

**Answers for Question 4**

**This is extra page for answers. Please indicate question number clearly.**